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		Application Number	10/604,245
		Filing Date	07/04/2003
		First Named Inventor	Wen-Huang Liu
		Art Unit	2811
		Examiner Name	HU, SHOUXIANG
Sheet 1	of 1	Attorney Docket Number	KYCP0010USA

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SR	1	CHEN-FU CHU et al., Fabrication and Characteristics of Freestanding GaN light emitting Devices by Laser Lift-off Technique, Proceedings of Opto-Electronics and Communications Conference, Jul. 8, 2002, No. 87, Yokohama, Japan	
	2	F. S. SHIEU et al., Effect of a Ti interlayer on the bond strength and thermal stability of the Cu/benzocyclobutene-divinyl tetramethyldisiloxane interface, J. Adhesion Sci. Technol., 1998, pp. 19-28, Vol. 12, No. 1, VSP, Netherlands	
	3	R. H. HORNG et al., AlGaInP light-emitting diodes with mirror substrates fabricated by wafer bonding, Applied Physics Letters, Nov. 15, 1999, pp. 3054-3056, Vol. 75, No. 20, American Institute of Physics, USA	
	4	G. DANG et al., Comparison of Dry and Wet Etch Processes for Patterning SiO ₂ /TiO ₂ Distributed Bragg Reflectors for Vertical-Cavity Surface-Emitting Lasers, Journal of The Electrochemical Society, 2001, G25-G28, Vol., 148(2), The Electrochemical Society, Inc., NJ, USA	
	5	T. MARGALITH et al., Indiumtin oxidecontacts to gallium nitride optoelectronic devices, Applied Physics Letters, Jun. 28, 1999, pp. 3930-3932, Vol. 74, No. 26, American institute of Physics, USA	

Examiner Signature	<i>Shouxiang Hu</i>	Date Considered	6/07/05
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